L Number	Hits	Soarch Mout	DB	Time stamp
1	5362	Search Text ((438/30) or (438/128) or (438/149) or	USPAT;	2004/09/30 20:58
<u> </u>		(438/488) or (438/489) or (438/491) or	US-PGPUB;	
]		(438/795)).CCLS.	EPO; JPO;	
			DERWENT;	
2	28	(((438/30) or (438/128) or (438/149) or	IBM_TDB USPAT;	2004/09/30 21:02
_	20	(438/488) or (438/489) or (438/491) or	US-PGPUB;	2004/03/30 21:02
		(438/795)).CCLS.) and (intermittent\$3 same	EPO; JPO;	
		irradiat\$4)	DERWENT;	
	_	///420/20\ /420/100\ /420/140\	IBM_TDB	0004/00/00 01 00
3	1	(((438/30) or (438/128) or (438/149) or (438/488) or (438/489) or (438/491) or	USPAT; US-PGPUB;	2004/09/30 21:02
		(438/795)).CCLS.) and ((intermittent\$3	EPO; JPO;	
		same irradiat\$4) same peripheral near2	DERWENT;	
		side\$1)	IBM_TDB	
-	4841	, , , , , , , , , , , , , , , , , , ,	USPAT;	2004/09/30 20:57
		(438/488) or (438/489) or (438/491) or (438/795)).CCLS.	US-PGPUB; EPO; JPO;	
		(430779377.00113.	DERWENT;	
			IBM TDB	
-	0	quasi near2 strip near2 like near2 crystal	USPĀT;	2004/01/11 22:35
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	2	quasi near2 strip near2 like	USPĀT;	2004/01/11 21:24
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	1188	polycrystalline same recrystallization	USPĀT;	2004/01/11 21:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	0	(((438/30) or (438/128) or (438/149) or	USPAT;	2004/01/11 21:25
		(438/488) or (438/489) or (438/491) or	US-PGPUB;	·
		(438/795)).CCLS.) and (quasi near2 strip near2 like)	EPO; JPO;	
		nearz like)	DERWENT; IBM TDB	
-	7080	reformation	USPAT;	2004/01/11 21:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	83908	polycrystalline	USPAT;	2004/01/11 22:21
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
-	6	reformation same polycrystalline	USPĀT;	2004/01/11 21:27
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
	84120	polycrystalline or (p adj si adj (layer or	USPAT;	2004/01/11 22:30
		film))	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	156387	anneal or annealing	USPAT;	2004/01/11 21:29
			US-PGPUB;	====, ==, ==, =========================
			EPO; JPO;	
			DERWENT;	
_	5374	(polycrystalline or (p adj si adj (layer	IBM_TDB USPAT;	2004/01/11 21:29
	55,4	or film)) same (anneal or annealing)	US-PGPUB;	2004/01/11 21:29
			EPO; JPO;	
			DERWENT;	
L			IBM_TDB	

Page 1

	C01 C00		I HODAM:	1 2004 (05 (14 10 27)
_	681508	laser	USPAT; US-PGPUB;	2004/05/14 19:37
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1662		USPAT;	2004/01/11 21:30
		adj (layer or film))) same (anneal or	US-PGPUB;	
		annealing))	EPO; JPO;	
			DERWENT;	
<u> </u>	2666	lateral near2 growth	IBM_TDB USPAT;	2004/01/11 21:30
	2000	laceral nearz growch	US-PGPUB;	2004/01/11 21:30
			EPO; JPO;	
			DERWENT;	
		·	IBM TDB	
-	23	(laser same ((polycrystalline or (p adj si	USPĀT;	2004/01/11 21:30
		adj (layer or film))) same (anneal or	US-PGPUB;	
		annealing))) same (lateral near2 growth)	EPO; JPO;	
			DERWENT;	
	-	(/#200242222#\	IBM_TDB	2004/01/11 01 30
1 -	5	(("200243222") or ("2002100637")).PN.	USPAT; US-PGPUB;	2004/01/11 21:39
1	1		EPO; JPO;	
	1		DERWENT;	
			IBM TDB	
-	202391	irradiate or irradiating	USPAT;	2004/05/14 19:34
	1		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		/:	IBM_TDB	0004/01/11 00 01
_	89	(irradiate or irradiating) near (polycrystalline or (p adj si adj (layer	USPAT; US-PGPUB;	2004/01/11 22:21
		or film)))	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	5342	((438/30) or (438/128) or (438/149) or	USPĀT;	2004/01/11 22:17
ĺ		(438/166) or (438/488) or (438/489) or	US-PGPUB;	
Ì		(438/491) or (438/795)).CCLS.	EPO; JPO;	
ł			DERWENT;	
_	26893	reform or reformation	IBM_TDB USPAT;	2004/01/11 22:19
	20033	Telefill of Telefillation	US-PGPUB;	2004/01/11 22.19
			EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
-	0	((irradiate or irradiating) near	USPĀT;	2004/01/11 22:19
	1	(polycrystalline or (p adj si adj (layer	US-PGPUB;	
	İ	or film)))) same (reform or reformation)	EPO; JPO;	.
			DERWENT; IBM TDB	
l _	0	((irradiate or irradiating) near	USPAT;	2004/01/11 22:19
	1	(polycrystalline or (p adj si adj (layer	US-PGPUB;	
		or film)))) and (reform or reformation)	EPO; JPO;	
		, in the second	DERWENT;	
			IBM_TDB	
-	25571	pulse near laser	USPAT;	2004/01/11 22:21
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	369	(pulse near laser) same (polycrystalline	USPAT;	2004/01/11 22:22
		or (p adj si adj (layer or film)))	US-PGPUB;	
		· · ·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	177	· · · · · · · · · · · · · · · · · · ·	USPAT;	2004/01/11 22:22
		or (p adj si adj (layer or film)))) and	US-PGPUB;	
		(irradiate or irradiating)	EPO; JPO; DERWENT;	
			IBM TDB	
·	L		1 2011 100	<u> </u>

-	41017	(polycrystalline or (p adj si)) near2	USPAT;	2004/05/14 19:33
		(layer or film)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	41	selective near irradiating	IBM_TDB USPAT;	2004/01/11 22:34
-	. 41	Selective hear irradiating	US-PGPUB;	2004/01/11 22:34
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1	((polycrystalline or (p adj si)) near2	USPAT;	2004/01/11 22:32
	_	(layer or film)) and (selective near	US-PGPUB;	2001,01,11 22.01
		irradiating)	EPO; JPO;	
		,	DERWENT;	
			IBM TDB	
-	17	(irradiate or irradiating) near (selective	USPĀT;	2004/01/11 22:35
		near irradiating)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	((irradiate or irradiating) near	USPAT;	2004/01/11 22:35
		((polycrystalline or (p adj si)) near2	US-PGPUB;	
1		(layer or film))) and (quasi near like)	EPO; JPO;	
			DERWENT;	ŀ
			IBM_TDB	
-	104	1 ,,	USPAT;	2004/01/11 22:40
		((polycrystalline or (p adj si)) near2	US-PGPUB;	
		(layer or film))	EPO; JPO;	
			DERWENT;	
	101		IBM_TDB	2004/01/11 02 41
-	101		USPAT;	2004/01/11 22:41
1		solidification	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	55	 (sequential near lateral near	USPAT;	2004/01/11 22:42
_)))	solidification) and ((polycrystalline or	US-PGPUB;	2004/01/11 22.42
		(p adj si)) near2 (layer or film))	EPO; JPO;	
		(p dd) 51// Mediz (idyel of 111m/ /	DERWENT;	
			IBM TDB	
_	103	quasi near like	USPĀT;	2004/01/12 10:20
		•	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	(("20010026835") or ("20020031876")).PN.	USPAT;	2004/05/14 16:03
			US-PGPUB	
-	5077		USPAT;	2004/05/14 19:32
		(438/488) or (438/489) or (438/491) or	US-PGPUB;	
		(438/795)).CCLS.	EPO; JPO;	
1	1		DERWENT;	
_	42208	(nolverystalling or (nodicity)	IBM_TDB USPAT;	2004/05/14 10:33
-	42208	(polycrystalline or (p adj si)) near2 (layer or film)	USPAT; US-PGPUB;	2004/05/14 19:33
1	1	(Tayer Or TITM)	EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
_	354399	irradiate or irradiating or irradiation	USPAT;	2004/05/14 19:34
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	255093	1 4	USPĀT;	2004/05/14 19:35
		crystallization or recrystallize or	US-PGPUB;	
		recrystallizing or recrystallization	EPO; JPO;	
			DERWENT;	
		<u> </u>	IBM_TDB	000440#/::::::::::::::::::::::::::::::::
-	23926	• • • • • • • • • • • • • • • • • • •	USPAT;	2004/05/14 19:36
		near (film or layer)	US-PGPUB;	
	1		EPO; JPO;	
	1		DERWENT;	
	L		IBM TDB	

	711816	lagon	I II CDAM.	2004/05/14 10:22
-	/11916	laser	USPAT; US-PGPUB;	2004/05/14 19:37
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	163809	anneal or annealing	USPAT;	2004/05/14 19:37
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	4110	((polycrystalline or (p adj si)) near2	USPAT;	2004/05/14 19:37
		(layer or film)) and (irradiate or	US-PGPUB;	
	1	irradiating or irradiation)	EPO; JPO;	
			DERWENT; IBM TDB	
i -	1995	(((polycrystalline or (p adj si)) near2	USPAT;	2004/05/14 19:37
		(layer or film)) and (irradiate or	US-PGPUB;	=====================================
		irradiating or irradiation)) and	EPO; JPO;	
		(crystallize or crystallizing or	DERWENT;	
		crystallization or recrystallize or recrystallizing or recrystallization)	IBM_TDB	
-	1384	((((polycrystalline or (p adj si)) near2	USPAT;	2004/05/14 19:37
1		(layer or film)) and (irradiate or	US-PGPUB;	2001/03/11 13.37
		irradiating or irradiation)) and	EPO; JPO;	
		(crystallize or crystallizing or	DERWENT;	
	İ	crystallization or recrystallize or	IBM_TDB	
		recrystallizing or recrystallization)) and (((a adj si) or (amorphous near2 silicon))		
		near (film or layer))		
_	1311		USPAT;	2004/05/14 19:37
		(layer or film)) and (irradiate or	US-PGPUB;	
		irradiating or irradiation)) and	EPO; JPO;	
		(crystallize or crystallizing or	DERWENT;	
		crystallization or recrystallize or recrystallization)) and	IBM_TDB	
		(((a adj si) or (amorphous near2 silicon))		
		near (film or layer))) and laser		
-	1154	((((((polycrystalline or (p adj si)) near2	USPAT;	2004/05/14 19:38
		(layer or film)) and (irradiate or	US-PGPUB;	
		irradiating or irradiation)) and (crystallize or crystallizing or	EPO; JPO; DERWENT;	
		crystallization or recrystallize or	IBM TDB	
		recrystallizing or recrystallization)) and		
		(((a adj si) or (amorphous near2 silicon))		
		near (film or layer))) and laser) and (anneal or annealing)		
_	208	(anneal or annealing) ((((((polycrystalline or (p adj si))	USPAT;	2004/05/14 19:40
	200	near2 (layer or film)) and (irradiate or	US-PGPUB;	2004/03/14 15:40
		irradiating or irradiation)) and	EPO; JPO;	
		(crystallize or crystallizing or	DERWENT;	
		crystallization or recrystallize or	IBM_TDB	
1		<pre>recrystallizing or recrystallization)) and (((a adj si) or (amorphous near2 silicon))</pre>		
]		near (film or layer))) and laser) and		
1		(anneal or annealing)) and (((438/30) or		
		(438/128) or (438/149) or (438/488) or		
		(438/489) or (438/491) or		
_	37776	(438/795)).CCLS.) active near2 matrix	HCDAM -	2004/05/14 10 15
-	3///0	active Heals Mattix	USPAT; US-PGPUB;	2004/05/14 19:40
			EPO; JPO;	
			DERWENT;	
L			IBM TDB	

near2 (layer or film)) and (irradiate or irradiating or irradiation) and (crystallize or crystallizing or crystallization or recrystallization)) and (((a adj si) or (amorphous near2 silicon)) near (film or layer))) and laser) and (anneal or annealing)) and (((438/30) or (438/128) or (438/149) or (438/488) or (438/49) or (438/491) or (438/49) or (438/48) or (438/128) or (438/49) or (438/48) or (438/489) or (438/49) or (4				
133		near2 (layer or film)) and (irradiate or irradiating or irradiation)) and (crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallizing or recrystallization)) and (((a adj si) or (amorphous near2 silicon)) near (film or layer))) and laser) and (anneal or annealing)) and (((438/30) or (438/128) or (438/149) or (438/488) or (438/795)).CCLS.)) and (active near2 matrix)	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/14 19:40
near2 (layer or film) and (irradiate or irradiating or irradiation) and (crystallize or crystallizing or crystallization or recrystallization) and (((a adj si) or (amorphous near2 silicon)) near (film or layer))) and laser) and (anneal or annealing) and (((438/30) or (438/128) or (438/491) or (438/489) or (438/491) or (438/795)).CCLS.)) and (active near2 matrix)) and (channel near2 region) pixel near2 region 71 ((((((((((polycrystalline or (p adj si)) near2 (layer or film)) and (irradiate or irradiating or irradiation)) and (crystallize or crystallization) and (((a adj si) or (amorphous near2 silicon)) near (film or layer))) and laser) and (anneal or annealing)) and (((438/30) or (438/128) or (438/149) or (438/488) or	- 59.	309 channel near2 region	US-PGPUB; EPO; JPO; DERWENT;	2004/05/14 19:41
US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; (((((((((((polycrystalline or (p adj si)) near2 (layer or film)) and (irradiate or irradiating or irradiation)) and (crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization)) and (((a adj si) or (amorphous near2 silicon)) near (film or layer)) and laser) and (anneal or annealing)) and (((438/30) or (438/128) or (438/149) or (438/488) or		near2 (layer or film)) and (irradiate or irradiating or irradiation)) and (crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization)) and (((a adj si) or (amorphous near2 silicon)) near (film or layer))) and laser) and (anneal or annealing)) and (((438/30) or (438/128) or (438/149) or (438/489) or (438/491) or (438/795)).CCLS.)) and (active near2	US-PGPUB; EPO; JPO; DERWENT;	2004/05/14 19:41
near2 (layer or film)) and (irradiate or irradiating or irradiation)) and (crystallize or crystallizing or crystallize or crystallize or recrystallization or recrystallization)) and (((a adj si) or (amorphous near2 silicon)) near (film or layer))) and laser) and (anneal or annealing)) and (((438/30) or (438/128) or (438/149) or (438/488) or	_ 17		US-PGPUB; EPO; JPO; DERWENT;	2004/05/14 19:41
(438/795)).CCLS.)) and (active near2 matrix)) and (channel near2 region)) and (pixel near2 region)		near2 (layer or film)) and (irradiate or irradiating or irradiation)) and (crystallize or crystallizing or crystallization or recrystallize or recrystallizing or recrystallization)) and (((a adj si) or (amorphous near2 silicon)) near (film or layer))) and laser) and (anneal or annealing)) and (((438/30) or (438/128) or (438/149) or (438/488) or (438/795)).CCLS.)) and (active near2 matrix)) and (channel near2 region)) and	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/14 19:41